

FY23 Topic Areas Research and Technology Development (TRTD)

A Novel X-ray Imaging Detector Concept: Stackable Photonic Crystal Scintillators with Perimetric Edge-On Detector Array

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OBJECTIVE

- Develop a novel X-ray imaging detector architecture, which introduces perimetric charge coupled device arrays as pixels integrated laterally.
- Offering a single imaging detector having energy resolving capability with high spatial resolution in broad X-ray energy regimes.

MOTIVATION

- Filling the technology gaps prioritized by the "Decadal Survey on Astronomy and Astrophysics in 2020s."
- Using a photonic crystal structure collimating and guiding the scintillation in an in-plane geometry^[1].
- A novel concept with perimetric pixels, which unnecessiates 2D CCD/CMOS coupled at the back, and enables the stacking of thin film layers of a variety of scintillators.
- An opportunity for flexible (polyvinyl-toluene) imaging detector application for better optical-angular-coupling efficiency.
- Polarization-sensitive imaging capability.

Scintillator

Metal Contac

Edge-on

Detector

FABRICATION Two main steps of fabrication;

- E-beam lithography for patterning and Inductively Coupled Plasma (ICP) etching to realize photonic crystal structure.
- The integration of perimetric CCDs via multi-stage wafer processing; deposition of the hard-mask layer, lithography, etch, regrowth of the CCD architecture, wet-etch for the lift-off of the excess layers.





DESIGN

Photonic

Crystal Structure

- 2-dimensional photonic crystal structure, which consists periodic cylindrical air holes.
- 150nm unit cell size of Photonic crystal media, with ~ 500 nm thick scintillator thin films.

Edge-on detectors integrated laterally Detector to the active scintillation layers.

- A simple p-i-n structure for perimetric pixels.
 - Multilayer architecture of variety of stacked thin film scintillators.





Photonic Crystal Unit Cell



The spatial resolution parameters, which refer to the FWHM of the beam wavefronts for some scintillators are shown in the left figure. The illustration of the self-collimation in BaF₂ PhC is shown in the visual on the right.

SIMULATIONS

For computing the band structures, or dispersion relations, and electromagnetic modes of periodic
dielectric structures.



For computing Fourier transforms based finitedifference time and frequency simulations for the validation of the self-collimating PhC structures.



GaN



(LEFT): GaN wafer: 5um epi-GaN on Sapphire substrate which has X-ray induced emission peaks around 400 nm (10%) and 550 nm (90%). (RIGHT): The SEM image of very first fabrication iterations. A successful fabrication of uniform, anisotropic cylindrical air holes with such a high aspect ratio of 1:20, thickness of ~2um.



Various illustrations regarding testing and characterization. The main graph shows the spectrum of light emissions from plain and PhC GaN upon deep-UV excitation. The illustrative images on the left side show different test and characterization setups based on material and the source. The two inset figures on the right show the spectrum of emitted light based on monochromatic (366nm) UV excitation.

References:

[1] Yasar, F., Kilin, M., Dehdashti, S., Yu, Z., Ma, Z., & Wang, Z. (2021). Spatially resolved x-ray detection with photonic crystal scintillators. Journal of Applied Physics, 130(4), 043101.

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[3] Varney, C. R., et al. "X-ray luminescence based spectrometer for investigation of scintillation properties." Review of Scientific Instruments 83.10 (2012): 103112.

[4] Yanagida, Takayuki, et al. "Photoluminescence and scintillation properties GaN." Applied Physics Express 14.8 (2021): 082006

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